2SC5081

Silicon NPN Epitaxial

HITACHI

ADE-208-1133A (Z) 2nd. Edition Mar. 2001

Application

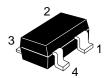
VHF / UHF wide band amplifier

Features

- High gain bandwidth product f_T = 13.5 GHz Typ
- High gain, low noise figure
 PG = 18 dB Typ, NF = 1.1 dB Typ at f = 900 MHz

Outline

CMPAK-4



- 1. Collector
- 2. Emitter
- 3. Base
- 4. Emitter

Note: Marking is "ZD-".

Attention: This device is very sensitive to electro static discharge.

It is recommended to adopt appropriate cautions when handling this transistor.



2SC5081

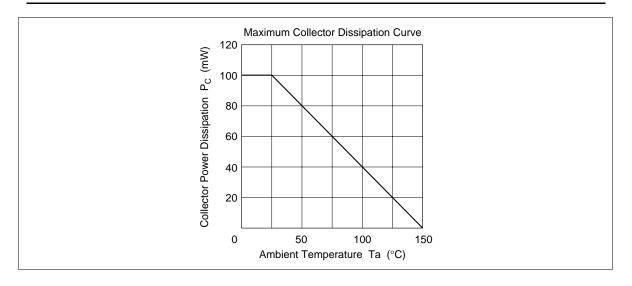
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V _{CEO}	8	V
Emitter to base voltage	V_{EBO}	1.5	V
Collector current	I _c	50	mA
Collector power dissipation	P _c	100	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Electrical Characteristics ($Ta = 25^{\circ}C$)

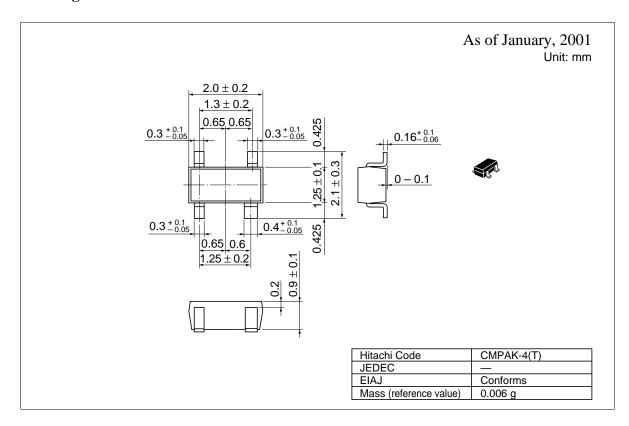
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	_	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector cutoff current	I _{CBO}	_	_	1	μΑ	$V_{CB} = 12 \text{ V}, I_{E} = 0$
	I _{CEO}	_	_	1	mA	$V_{CE} = 8 \text{ V}, R_{BE} = \infty$
Emitter cutoff current	I _{EBO}	_	_	10	μΑ	$V_{EB} = 1.5 \text{ V}, I_{C} = 0$
DC current transfer ratio	h_{FE}	50	90	160		$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA}$
Collector output capacitance	Cob	_	0.4	0.75	pF	$V_{CB} = 5 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$
Gain bandwidth product	f _T	10.5	13.5	_	GHz	$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA}$
Power gain	PG	15	18	_	dB	$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA},$ f = 900 MHz
Noise figure	NF	_	1.1	2.0	dB	$V_{CE} = 5 \text{ V}, I_{C} = 5 \text{ mA},$ f = 900 MHz

See characteristic curves of 2SC5080.



2SC5081

Package Dimensions



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